### 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Chip-Scale Package (CSP).

#### 2. Features and benefits

- Average forward current I<sub>F(AV)</sub> ≤ 0.5 A
- Reverse voltage V<sub>R</sub> ≤ 30 V
- Low forward voltage typ. V<sub>F</sub> = 310 mV
- Low reverse current typ. I<sub>R</sub> = 0.33 μA
- Package height typ. 0.3 mm

### 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Ultra high speed switching
- LED backlight for mobile application

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{amb} \le$ 105 °C; square wave	[1]	-	-	0.5	A
		$\delta$ = 0.5; f = 20 kHz; $T_{sp} \le$ 145 °C; square wave		-	-	0.5	A
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>F</sub>	forward voltage	$I_F$ = 10 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C		-	310	390	mV
I <sub>R</sub>	reverse current	$V_R$ = 10 V; $T_j$ = 25 °C; pulsed		-	0.33	2	μΑ
t <sub>rr</sub>	reverse recovery time	$I_F$ = 500 mA; $I_R$ = 500 mA; $I_{R(meas)}$ = 100 mA; $T_j$ = 25 °C		-	1.42	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB),  $Al_2O_3$ , standard footprint.





# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 - 1 - 2
2	Α	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

<sup>[1]</sup> The marking bar indicates the cathode.

# 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3005ESF	DSN0603-2	Leadless ultra small package; 2 terminals; body 0.6 x 0.3 x 0.3 mm	SOD962-2

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMEG3005ESF	7

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	30	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 140 °C; δ = 1		-	0.71	Α
I <sub>F(AV)</sub>	average forward current	$\bar{\delta}$ = 0.5; f = 20 kHz; $T_{amb} \leq$ 105 °C; square wave	[1]	-	0.5	A
		$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 145 °C; square wave		-	0.5	A
I <sub>FRM</sub>	repetitive peak forward current	$t_p = 1 \text{ ms}; \delta \le 0.25$		-	1.5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	3.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	405	mW
			[3]	-	660	mW
			[1]	-	1200	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistant from junction to ambient	thermal resistance		[1][2]	-	-	310	K/W
			[1][3]	-	-	190	K/W
	ambient		[1][4]	-	-	105	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	40	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of anode tab.

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#### 30 V, 0.5 A low VF MEGA Schottky barrier rectifier

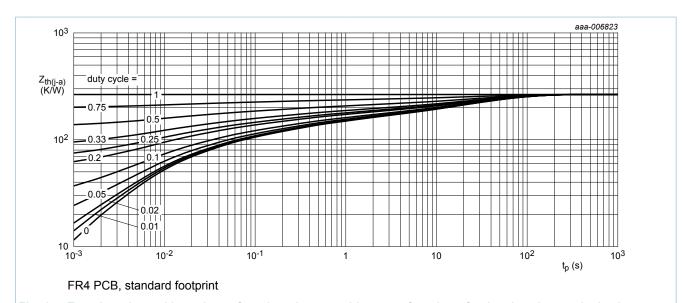
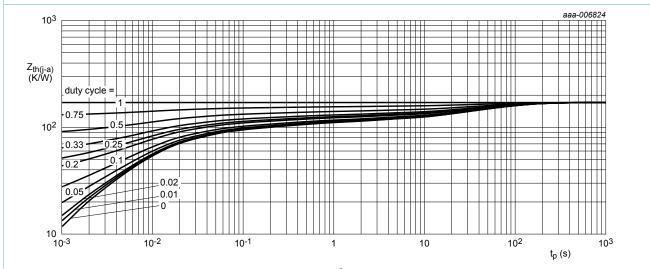


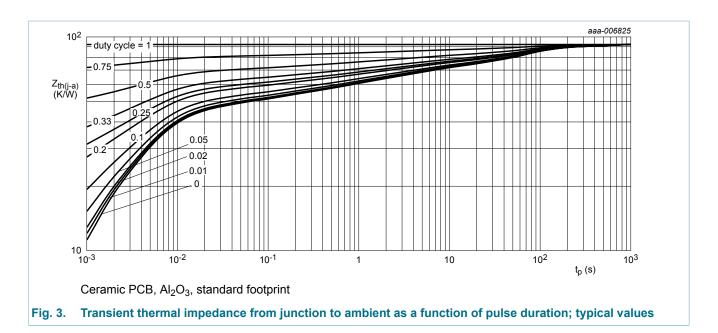
Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for anode and cathode 1 cm<sup>2</sup> each

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 30 V, 0.5 A low VF MEGA Schottky barrier rectifier



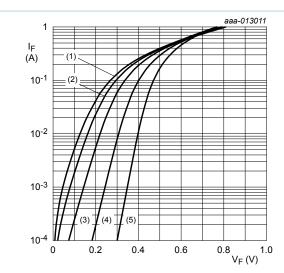
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### 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	$I_R$ = 100 μA; $t_p$ = 300 μs; $δ$ = 0.02; $T_j$ = 25 °C	30	-	-	V
V <sub>F</sub>	forward voltage	$I_F$ = 0.1 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C	-	185	255	mV
		$I_F$ = 1 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C	-	245	320	mV
	$I_F$ = 10 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C	· ·	-	310	390	mV
		$I_F$ = 100 mA; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_j$ = 25 °C	-	405	480	mV
		$I_F$ = 200 mA; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_j$ = 25 °C	-	460	535	mV
		$I_F$ = 500 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C	-	595	720	mV
I <sub>R</sub>	reverse current	$V_R = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ pulsed}$	-	0.33	2	μA
		$V_R = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	1.8	9	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	21	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	8	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F$ = 500 mA; $I_R$ = 500 mA; $I_{R(meas)}$ = 100 mA; $T_j$ = 25 °C	-	1.42	-	ns

#### 30 V, 0.5 A low VF MEGA Schottky barrier rectifier



pulsed condition

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 125 \, ^{\circ}C$ 

(3)  $T_j = 85 \, ^{\circ}C$ 

(4)  $T_i = 25 \, ^{\circ}C$ 

(5)  $T_i = -40 \, ^{\circ}C$ 

Fig. 4. Forward current as a function of forward voltage; typical values

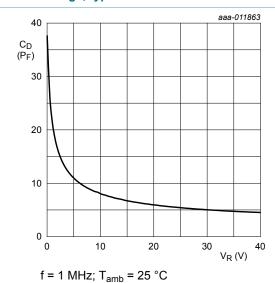
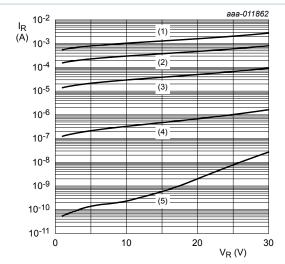


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



pulsed condition

(1)  $T_i = 150 \, ^{\circ}C$ 

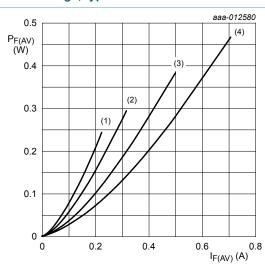
(2)  $T_i = 125 \,^{\circ}\text{C}$ 

(3)  $T_j = 85 \, ^{\circ}C$ 

(4)  $T_j = 25 \, ^{\circ}C$ 

(5)  $T_i = -40 \, ^{\circ}\text{C}$ 

Fig. 5. Reverse current as a function of reverse voltage; typical values



T<sub>i</sub> = 150 °C

 $(1) \delta = 0.1$ 

(2)  $\delta = 0.2$ 

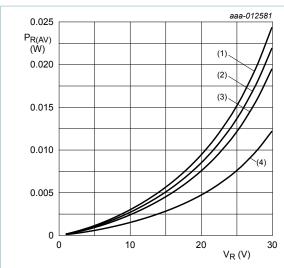
 $(3) \delta = 0.5$ 

 $(4) \delta = 1$ 

ig. 7. Average forward power dissipation as a function of average forward current; typical values

7/14

#### 30 V, 0.5 A low VF MEGA Schottky barrier rectifier



 $T_i = 125 \,{}^{\circ}\text{C}$ 

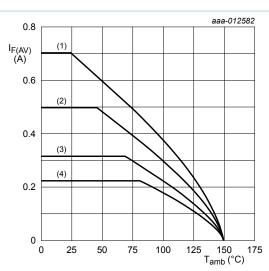
, (1) δ = 1

 $(2) \delta = 0.9$ 

 $(3) \delta = 0.8$ 

 $(4) \delta = 0.5$ 

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \,{}^{\circ}\text{C}$ 

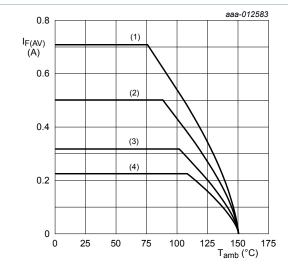
(1)  $\delta$  = 1; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for anode and cathode

1 cm<sup>2</sup> each

 $T_i = 150 \, ^{\circ}C$ 

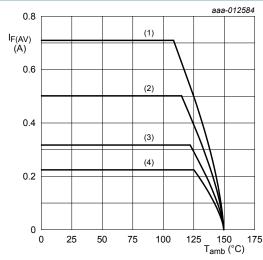
(1)  $\delta$  = 1; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 150 \,{}^{\circ}\text{C}$ 

(1)  $\delta$  = 1; DC

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

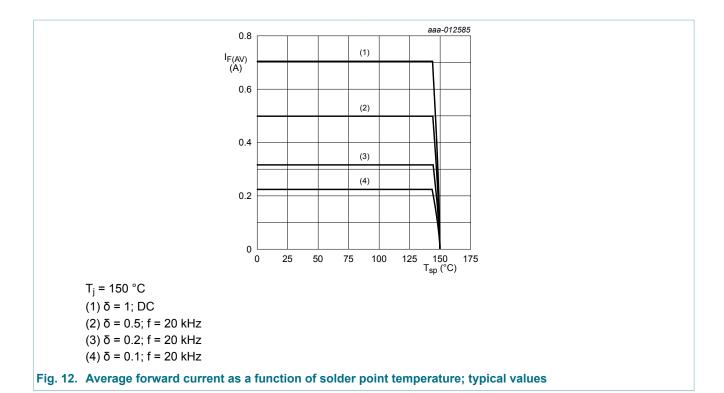
(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values

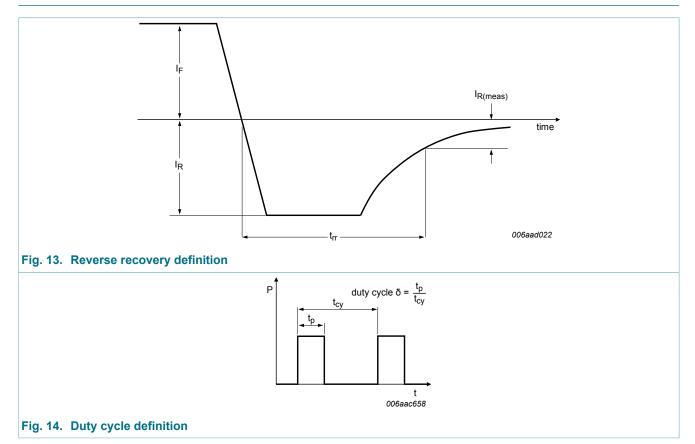
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### 11. Test information



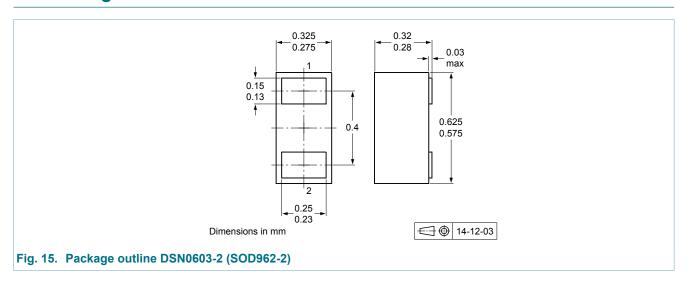
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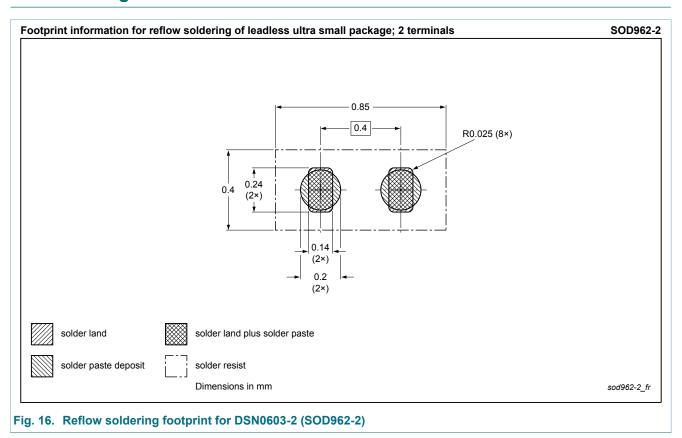
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The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 12. Package outline



### 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3005ESF v.2	20150206	Product data sheet	-	PMEG3005ESF v.1
Modifications:	<ul> <li>Product status char</li> </ul>	nged		
PMEG3005ESF v.1	20140512	Preliminary data sheet	-	-

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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### 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	3
10	Characteristics	6
11	Test information	9
12	Package outline	10
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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